

INFORMATION DISCLOSURE CITATION
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Docket Number (Optional)

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Application Number

10/639,942

Applicant(s)

Hussein I. Hanafi, et al.

Filing Date

August 13, 2003

Group Art Unit

2812

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SDI		6,580,132 B1	06/17/03	Chan, et al.			
		6,528,376 B1	03/04/03	Guo Jyh-Chyurn			
		6,339,002 B1	01/15/02	Chan, et al.			
		5,773,331 A	06/30/98	Wong Hon-Sum Philip, et al.			
		5,346,839 A	09/13/94	Sundaresan Ravishankar			

U.S. PATENT APPLICATION PUBLICATIONS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
SDI	WO 02/101811 A	19-12-02	PCT				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SDI	Guarini K W, et al., "Triple-self-aligned, planar double-gate MOSFETs: devices and circuits" International Electron Devices Meeting 2001. IEDM. Technical Digest. Washington, DC, Dec. 2-5, 2001, New York, NY: IEEE, US, 2 December 2001 (2001-12-02), pp 1921-1924.

EXAMINER

Stanette Haas

DATE CONSIDERED

10/28/05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.